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#### Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

#### **Applications of Embedded - FPGAs**

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
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Details	
Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	110592
Number of I/O	177
Number of Gates	600000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	256-LBGA
Supplier Device Package	256-FPBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/microsemi/a3p600l-fgg256i

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Flash\*Freeze Technology and Low Power Modes

power supply and board-level configurations, the user can easily calculate how long it will take for the core to become inactive or active. For more information, refer to the "Power-Up/-Down Behavior of Low Power Flash Devices" section on page 373.



Figure 2-8 • Entering and Exiting Sleep Mode, Typical Timing Diagram

### **Context Save and Restore in Sleep or Shutdown Mode**

In Sleep mode or Shutdown mode, the contents of the SRAM, state of the I/Os, and state of the registers are lost when the device is powered off, if no other measure is taken. A low-cost external serial EEPROM can be used to save and restore the contents of the device when entering and exiting Sleep mode or Shutdown mode. In the *Embedded SRAM Initialization Using External Serial EEPROM* application note, detailed information and a reference design are provided for initializing the embedded SRAM using an external serial EEPROM. The user can easily customize the reference design to save and restore the FPGA state when entering and exiting Sleep mode or Shutdown mode. The microcontroller will need to manage this activity; hence, before powering down  $V_{CC}$ , the data will be read from the FPGA and stored externally. In a similar way, after the FPGA is powered up, the microcontroller will allow the FPGA to load the data from external memory and restore its original state.

## Flash\*Freeze Design Guide

This section describes how designers can create reliable designs that use ultra-low power Flash\*Freeze modes optimally. The section below provides guidance on how to select the best Flash\*Freeze mode for any application. The "Design Solutions" section on page 35 gives specific recommendations on how to design and configure clocks, set/reset signals, and I/Os. This section also gives an overview of the design flow and provides details concerning Microsemi's Flash\*Freeze Management IP, which enables clean clock gating and housekeeping. The "Additional Power Conservation Techniques" section on page 41 describes board-level considerations for entering and exiting Flash\*Freeze mode.

### Selecting the Right Flash\*Freeze Mode

Both Flash\*Freeze modes will bring an FPGA into an ultra-low power static mode that retains register and SRAM content and sets I/Os to a predetermined configuration. There are two primary differences that distinguish type 2 mode from type 1, and they must be considered when creating a design using Flash\*Freeze technology.

First, with type 2 mode, the device has an opportunity to wait for a second signal to enable activation of Flash\*Freeze mode. This allows processes to complete prior to deactivating the device, and can be useful to control task completion, data preservation, accidental Flash\*Freeze activation, system shutdown, or any other housekeeping function. The second signal may be derived from an external or into-out internal source. The second difference between type 1 and type 2 modes is that a design for type 2 mode has an opportunity to cleanly manage clocks and data activity before entering and exiting Flash\*Freeze mode. This is particularly important when data preservation is needed, as it ensures valid data is stored prior to entering, and upon exiting, Flash\*Freeze mode.

Type 1 Flash\*Freeze mode is ideally suited for applications with the following design criteria:

- Entering Flash\*Freeze mode is not dependent on any signal other than the external FF pin.
- Internal housekeeping is not required prior to entering Flash\*Freeze.

ProASIC3L FPGA Fabric User's Guide

Date	Changes	Page					
v2.1 (October 2008)	The title changed from "Flash*Freeze Technology and Low Power Modes in IGLOO, IGLOO PLUS, and ProASIC3L Devices" to Actel's Flash*Freeze Technology and Low Power Modes."	N/A					
	The "Flash Families Support the Flash*Freeze Feature" section was updated.	22					
	Significant changes were made to this document to support Libero IDE v8.4 and later functionality. RT ProASIC3 device support information is new. In addition to the other major changes, the following tables and figures were updated or are new:						
	Figure 2-3 • Flash*Freeze Mode Type 2 – Controlled by Flash*Freeze Pin and Internal Logic (LSICC signal) – updated	27					
	Figure 2-5 • Narrow Clock Pulses During Flash*Freeze Entrance and Exit – new	00					
	Figure 2-10 • Flash*Freeze Management IP Block Diagram – new	30					
	Table 2-11 • FSM State Diagram – New	37 38					
	2)—I/O Pad State – updated	29					
	Please review the entire document carefully.						
v1.3 (June 2008)	The family description for ProASIC3L in Table 2-1 • Flash-Based FPGAs was updated to include 1.5 V.	22					
v1.2 (March 2008)	The part number for this document was changed from 51700094-003-1 to 51700094-004-2.	N/A					
	The title of the document was changed to "Flash*Freeze Technology and Low Power Modes in IGLOO, IGLOO PLUS, and ProASIC3L Devices."						
	The "Flash*Freeze Technology and Low Power Modes" section was updated to remove the parenthetical phrase, "from 25 $\mu$ W," in the second paragraph. The following sentence was added to the third paragraph: "IGLOO PLUS has an additional feature when operating in Flash*Freeze mode, allowing it to retain I/O states as well as SRAM and register states."	21					
	The "Power Conservation Techniques" section was updated to add $V_{JTAG}$ to the parenthetical list of power supplies that should be tied to the ground plane if unused. Additional information was added regarding how the software configures unused I/Os.	2-1					
	Table 2-1 • Flash-Based FPGAs and the accompanying text was updated to include the IGLOO PLUS family. The "IGLOO Terminology" section and "ProASIC3 Terminology" section are new.	22					
	The "Flash*Freeze Mode" section was revised to include that I/O states are preserved in Flash*Freeze mode for IGLOO PLUS devices. The last sentence in the second paragraph was changed to, "If the FF pin is not used, it can be used as a regular I/O." The following sentence was added for Flash*Freeze mode type 2: "Exiting the mode is controlled by either the FF pin OR the user-defined LSICC signal."	24					
	The "Flash*Freeze Type 1: Control by Dedicated Flash*Freeze Pin" section was revised to change instructions for implementing this mode, including instructions for implementation with Libero IDE v8.3.	24					
	Figure 2-1 • Flash*Freeze Mode Type 1 – Controlled by the Flash*Freeze Pin was updated.	25					
	The "Flash*Freeze Type 2: Control by Dedicated Flash*Freeze Pin and Internal Logic" section was renamed from "Type 2 Software Implementation."	26					
	The "Type 2 Software Implementation for Libero IDE v8.3" section is new.	2-6					

YB and YC are identical to GLB and GLC, respectively, with the exception of a higher selectable final output delay. The SmartGen PLL Wizard will configure these outputs according to user specifications and can enable these signals with or without the enabling of Global Output Clocks.

The above signals can be enabled in the following output groupings in both internal and external feedback configurations of the static PLL:

- One output GLA only
- Two outputs GLA + (GLB and/or YB)
- Three outputs GLA + (GLB and/or YB) + (GLC and/or YC)

### PLL Macro Block Diagram

As illustrated, the PLL supports three distinct output frequencies from a given input clock. Two of these (GLB and GLC) can be routed to the B and C global network access, respectively, and/or routed to the device core (YB and YC).

There are five delay elements to support phase control on all five outputs (GLA, GLB, GLC, YB, and YC). There are delay elements in the feedback loop that can be used to advance the clock relative to the reference clock.

The PLL macro reference clock can be driven in the following ways:

- By an INBUF\* macro to create a composite macro, where the I/O macro drives the global buffer (with programmable delay) using a hardwired connection. In this case, the I/O must be placed in one of the dedicated global I/O locations.
- 2. Directly from the FPGA core.
- 3. From an I/O that is routed through the FPGA regular routing fabric. In this case, users must instantiate a special macro, PLLINT, to differentiate from the hardwired I/O connection described earlier.

During power-up, the PLL outputs will toggle around the maximum frequency of the voltage-controlled oscillator (VCO) gear selected. Toggle frequencies can range from 40 MHz to 250 MHz. This will continue as long as the clock input (CLKA) is constant (HIGH or LOW). This can be prevented by LOW assertion of the POWERDOWN signal.

The visual PLL configuration in SmartGen, a component of the Libero SoC and Designer tools, will derive the necessary internal divider ratios based on the input frequency and desired output frequencies selected by the user.

This section outlines the following device information: CCC features, PLL core specifications, functional descriptions, software configuration information, detailed usage information, recommended board-level considerations, and other considerations concerning global networks in low power flash devices.

## **Clock Conditioning Circuits with Integrated PLLs**

Each of the CCCs with integrated PLLs includes the following:

- 1 PLL core, which consists of a phase detector, a low-pass filter, and a four-phase voltagecontrolled oscillator
- 3 global multiplexer blocks that steer signals from the global pads and the PLL core onto the global networks
- · 6 programmable delays and 1 fixed delay for time advance/delay adjustments
- 5 programmable frequency divider blocks to provide frequency synthesis (automatically configured by the SmartGen macro builder tool)

## **Clock Conditioning Circuits without Integrated PLLs**

There are two types of simplified CCCs without integrated PLLs in low power flash devices.

- 1. The simplified CCC with programmable delays, which is composed of the following:
  - 3 global multiplexer blocks that steer signals from the global pads and the programmable delay elements onto the global networks
  - 3 programmable delay elements to provide time delay adjustments
- 2. The simplified CCC (referred to as CCC-GL) without programmable delay elements, which is composed of the following:
  - A global multiplexer block that steer signals from the global pads onto the global networks

difference will cause the VCO to increase its frequency until the output signal is phase-identical to the input after undergoing division. In other words, lock in both frequency and phase is achieved when the output frequency is M times the input. Thus, clock division in the feedback path results in multiplication at the output.

A similar argument can be made when the delay element is inserted into the feedback path. To achieve steady-state lock, the VCO output signal will be delayed by the input period *less* the feedback delay. For periodic signals, this is equivalent to time-advancing the output clock by the feedback delay.

Another key parameter of a PLL system is the acquisition time. Acquisition time is the amount of time it takes for the PLL to achieve lock (i.e., phase-align the feedback signal with the input reference clock). For example, suppose there is no voltage applied to the VCO, allowing it to operate at its free-running frequency. Should an input reference clock suddenly appear, a lock would be established within the maximum acquisition time.

## **Functional Description**

This section provides detailed descriptions of PLL block functionality: clock dividers and multipliers, clock delay adjustment, phase adjustment, and dynamic PLL configuration.

## **Clock Dividers and Multipliers**

The PLL block contains five programmable dividers. Figure 4-20 shows a simplified PLL block.



Figure 4-20 • PLL Block Diagram

FlashROM in Microsemi's Low Power Flash Devices

## **FlashROM Design Flow**

The Microsemi Libero System-on-Chip (SoC) software has extensive FlashROM support, including FlashROM generation, instantiation, simulation, and programming. Figure 5-9 shows the user flow diagram. In the design flow, there are three main steps:

- 1. FlashROM generation and instantiation in the design
- 2. Simulation of FlashROM design
- 3. Programming file generation for FlashROM design



Figure 5-9 • FlashROM Design Flow

### FlashROM Generation and Instantiation in the Design

The SmartGen core generator, available in Libero SoC and Designer, is the only tool that can be used to generate the FlashROM content. SmartGen has several user-friendly features to help generate the FlashROM contents. Instead of selecting each byte and assigning values, you can create a region within a page, modify the region, and assign properties to that region. The FlashROM user interface, shown in Figure 5-10, includes the configuration grid, existing regions list, and properties field. The properties field specifies the region-specific information and defines the data used for that region. You can assign values to the following properties:

- Static Fixed Data—Enables you to fix the data so it cannot be changed during programming time. This option is useful when you have fixed data stored in this region, which is required for the operation of the design in the FPGA. Key storage is one example.
- Static Modifiable Data—Select this option when the data in a particular region is expected to be static data (such as a version number, which remains the same for a long duration but could conceivably change in the future). This option enables you to avoid changing the value every time you enter new data.
- 3. Read from File—This provides the full flexibility of FlashROM usage to the customer. If you have a customized algorithm for generating the FlashROM data, you can specify this setting. You can then generate a text file with data for as many devices as you wish to program, and load that into the FlashPoint programming file generation software to get programming files that include all the data. SmartGen will optionally pass the location of the file where the data is stored if the file is specified in SmartGen. Each text file has only one type of data format (binary, decimal, hex, or ASCII text). The length of each data file must be shorter than or equal to the selected region length. If the data is shorter than the selected region length, the most significant bits will be padded with 0s. For multiple text files for multiple regions, the first lines are for the first device. In SmartGen, Load Sim. Value From File allows you to load the first device data in the MEM file for simulation.
- 4. Auto Increment/Decrement—This scenario is useful when you specify the contents of FlashROM for a large number of devices in a series. You can specify the step value for the serial number and a maximum value for inventory control. During programming file generation, the actual number of devices to be programmed is specified and a start value is fed to the software.

Figure 5-10 • SmartGen GUI of the FlashROM

SRAM and FIFO Memories in Microsemi's Low Power Flash Devices

#### Table 6-2 • Allowable Aspect Ratio Settings for WIDTHA[1:0]

WIDTHA[1:0]	WIDTHB[1:0]	D×W
00	00	4k×1
01	01	2k×2
10	10	1k×4
11	11	512×9

Note: The aspect ratio settings are constant and cannot be changed on the fly.

### BLKA and BLKB

These signals are active-low and will enable the respective ports when asserted. When a BLKx signal is deasserted, that port's outputs hold the previous value.

# Note: When using the SRAM in single-port mode for Automotive ProASIC3 devices, BLKB should be tied to ground.

#### WENA and WENB

These signals switch the RAM between read and write modes for the respective ports. A LOW on these signals indicates a write operation, and a HIGH indicates a read.

Note: When using the SRAM in single-port mode for Automotive ProASIC3 devices, WENB should be tied to ground.

### **CLKA and CLKB**

These are the clock signals for the synchronous read and write operations. These can be driven independently or with the same driver.

Note: For Automotive ProASIC3 devices, dual-port mode is supported if the clocks to the two SRAM ports are the same and 180° out of phase (i.e., the port A clock is the inverse of the port B clock). For use of this macro as a single-port SRAM, the inputs and clock of one port should be tied off (grounded) to prevent errors during design compile.

### PIPEA and PIPEB

These signals are used to specify pipelined read on the output. A LOW on PIPEA or PIPEB indicates a nonpipelined read, and the data appears on the corresponding output in the same clock cycle. A HIGH indicates a pipelined read, and data appears on the corresponding output in the next clock cycle.

Note: When using the SRAM in single-port mode for Automotive ProASIC3 devices, PIPEB should be tied to ground. For use in dual-port mode, the same clock with an inversion between the two clock pins of the macro should be used in the design to prevent errors during compile.

#### WMODEA and WMODEB

These signals are used to configure the behavior of the output when the RAM is in write mode. A LOW on these signals makes the output retain data from the previous read. A HIGH indicates pass-through behavior, wherein the data being written will appear immediately on the output. This signal is overridden when the RAM is being read.

# Note: When using the SRAM in single-port mode for Automotive ProASIC3 devices, WMODEB should be tied to ground.

#### RESET

This active-low signal resets the control logic, forces the output hold state registers to zero, disables reads and writes from the SRAM block, and clears the data hold registers when asserted. It does not reset the contents of the memory array.

While the RESET signal is active, read and write operations are disabled. As with any asynchronous reset signal, care must be taken not to assert it too close to the edges of active read and write clocks.

### ADDRA and ADDRB

These are used as read or write addresses, and they are 12 bits wide. When a depth of less than 4 k is specified, the unused high-order bits must be grounded (Table 6-3 on page 155).

### Solution 4

The board-level design must ensure that the reflected waveform at the pad does not exceed the voltage overshoot/undershoot limits provided in the datasheet. This is a requirement to ensure long-term reliability.



Figure 7-12 • Solution 4

I/O Structures in IGLOO and ProASIC3 Devices

## Simultaneously Switching Outputs (SSOs) and Printed Circuit Board Layout

Each I/O voltage bank has a separate ground and power plane for input and output circuits (VMV/GNDQ for input buffers and VCCI/GND for output buffers). This isolation is necessary to minimize simultaneous switching noise from the input and output (SSI and SSO). The switching noise (ground bounce and power bounce) is generated by the output buffers and transferred into input buffer circuits, and vice versa.

Since voltage bounce originates on the package inductance, the VMV and VCCI supplies have separate package pin assignments. For the same reason, GND and GNDQ also have separate pin assignments.

The VMV and VCCI pins must be shorted to each other on the board. Also, the GND and GNDQ pins must be shorted to each other on the board. This will prevent unwanted current draw from the power supply.

SSOs can cause signal integrity problems on adjacent signals that are not part of the SSO bus. Both inductive and capacitive coupling parasitics of bond wires inside packages and of traces on PCBs will transfer noise from SSO busses onto signals adjacent to those busses. Additionally, SSOs can produce ground bounce noise and VCCI dip noise. These two noise types are caused by rapidly changing currents through GND and VCCI package pin inductances during switching activities (EQ 2 and EQ 3).

Ground bounce noise voltage = L(GND) × di/dt

VCCI dip noise voltage = L(VCCI) × di/dt

EQ 3

EQ 2

Any group of four or more input pins switching on the same clock edge is considered an SSO bus. The shielding should be done both on the board and inside the package unless otherwise described.

In-package shielding can be achieved in several ways; the required shielding will vary depending on whether pins next to the SSO bus are LVTTL/LVCMOS inputs, LVTTL/LVCMOS outputs, or GTL/SSTL/HSTL/LVDS/LVPECL inputs and outputs. Board traces in the vicinity of the SSO bus have to be adequately shielded from mutual coupling and inductive noise that can be generated by the SSO bus. Also, noise generated by the SSO bus needs to be reduced inside the package.

PCBs perform an important function in feeding stable supply voltages to the IC and, at the same time, maintaining signal integrity between devices.

Key issues that need to be considered are as follows:

- · Power and ground plane design and decoupling network design
- Transmission line reflections and terminations

For extensive data per package on the SSO and PCB issues, refer to the "ProASIC3/E SSO and Pin Placement and Guidelines" chapter of the *ProASIC3 FPGA Fabric User's Guide*.



I/O Structures in IGLOOe and ProASIC3E Devices

### 5 V Output Tolerance

IGLOO and ProASIC3 I/Os must be set to 3.3 V LVTTL or 3.3 V LVCMOS mode to reliably drive 5 V TTL receivers. It is also critical that there be NO external I/O pull-up resistor to 5 V, since this resistor would pull the I/O pad voltage beyond the 3.6 V absolute maximum value and consequently cause damage to the I/O.

When set to 3.3 V LVTTL or 3.3 V LVCMOS mode, the I/Os can directly drive signals into 5 V TTL receivers. In fact, VOL = 0.4 V and VOH = 2.4 V in both 3.3 V LVTTL and 3.3 V LVCMOS modes exceeds the VIL = 0.8 V and VIH = 2 V level requirements of 5 V TTL receivers. Therefore, level 1 and level 0 will be recognized correctly by 5 V TTL receivers.

## **Schmitt Trigger**

A Schmitt trigger is a buffer used to convert a slow or noisy input signal into a clean one before passing it to the FPGA. Using Schmitt trigger buffers guarantees a fast, noise-free input signal to the FPGA.

ProASIC3E devices have Schmitt triggers built into their I/O circuitry. The Schmitt trigger is available for the LVTTL, LVCMOS, and 3.3 V PCI I/O standards.

This feature can be implemented by using a Physical Design Constraints (PDC) command (Table 8-6 on page 218) or by selecting a check box in the I/O Attribute Editor in Designer. The check box is cleared by default.

### Selectable Skew between Output Buffer Enable and Disable Times

Low power flash devices have a configurable skew block in the output buffer circuitry that can be enabled to delay output buffer assertion without affecting deassertion time. Since this skew block is only available for the OE signal, the feature can be used in tristate and bidirectional buffers. A typical 1.2 ns delay is added to the OE signal to prevent potential bus contention. Refer to the appropriate family datasheet for detailed timing diagrams and descriptions.

The Skew feature is available for all I/O standards.

This feature can be implemented by using a PDC command (Table 8-6 on page 218) or by selecting a check box in the I/O Attribute Editor in Designer. The check box is cleared by default.

The configurable skew block is used to delay output buffer assertion (enable) without affecting deassertion (disable) time.





I/O Structures in IGLOOe and ProASIC3E Devices

# Table 8-18 • Supported IGLOOe, ProASIC3L, and ProASIC3E I/O Standards and Corresponding VREF and VTT Voltages

I/O Standard	Input/Output Supply Voltage (VMV <sub>TYP</sub> /V <sub>CCI_TYP</sub> )	Input Reference Voltage (V <sub>REF_TYP</sub> )	Board Termination Voltage (V <sub>TT_TYP</sub> )
LVTTL/ L VCMOS 3.3 V	3.30 V	-	_
LVCMOS 2.5 V	2.50 V	-	_
LVCMOS 2.5/5.0 V Input	2.50 V	-	-
LVCMOS 1.8 V	1.80 V	-	-
LVCMOS 1.5 V	1.50 V	-	_
PCI 3.3 V	3.30 V	-	-
PCI-X 3.3 V	3.30 V	-	-
GTL+ 3.3 V	3.30 V	1.00 V	1.50 V
GTL+ 2.5 V	2.50 V	1.00 V	1.50 V
GTL 3.3 V	3.30 V	0.80 V	1.20 V
GTL 2.5 V	2.50 V	0.80 V	1.20 V
HSTL Class I	1.50 V	0.75 V	0.75 V
HSTL Class II	1.50 V	0.75 V	0.75 V
SSTL3 Class I	3.30 V	1.50 V	1.50 V
SSTL3 Class II	3.30 V	1.50 V	1.50 V
SSTL2 Class I	2.50 V	1.25 V	1.25 V
SSTL2 Class II	2.50 V	1.25 V	1.25 V
LVDS, DDR LVDS, B-LVDS, M-LVDS	2.50 V	-	-
LVPECL	3.30 V	-	_

### I/O Bank Resource Usage

This is an important portion of the report. The user must meet the requirements stated in this table. Figure 9-10 shows the I/O Bank Resource Usage table included in the I/O bank report:

#### Figure 9-10 • I/O Bank Resource Usage Table

The example in Figure 9-10 shows that none of the I/O macros is assigned to the bank because more than one VCCI is detected.

### I/O Voltage Usage

The I/O Voltage Usage table provides the number of VREF (E devices only) and  $V_{CCI}$  assignments required in the design. If the user decides to make I/O assignments manually (PDC or MVN), the issues listed in this table must be resolved before proceeding to Layout. As stated earlier, VREF assignments must be made if there are any voltage-referenced I/Os.

Figure 9-11 shows the I/O Voltage Usage table included in the I/O bank report.

### Figure 9-11 • I/O Voltage Usage Table

The table in Figure 9-11 indicates that there are two voltage-referenced I/Os used in the design. Even though both of the voltage-referenced I/O technologies have the same VCCI voltage, their VREF voltages are different. As a result, two I/O banks are needed to assign the VCCI and VREF voltages.

In addition, there are six single-ended I/Os used that have the same VCCI voltage. Since two banks are already assigned with the same VCCI voltage and there are enough unused bonded I/Os in

I/O Software Control in Low Power Flash Devices

VREF for GTL+ 3.3 V

### Figure 9-13 • Selecting VREF Voltage for the I/O Bank

### **Assigning VREF Pins for a Bank**

The user can use default pins for VREF. In this case, select the **Use default pins for VREFs** check box (Figure 9-13). This option guarantees full VREF coverage of the bank. The equivalent PDC command is as follows:

set\_vref\_default [bank name]

To be able to choose VREF pins, adequate VREF pins must be created to allow legal placement of the compatible voltage-referenced I/Os.

To assign VREF pins manually, the PDC command is as follows:

set\_vref -bank [bank name] [package pin numbers]

For ChipPlanner/PinEditor to show the range of a VREF pin, perform the following steps:

- 1. Assign VCCI to a bank using **MVN > Edit > I/O Bank Settings**.
- 2. Open ChipPlanner. Zoom in on an I/O package pin in that bank.
- 3. Highlight the pin and then right-click. Choose Use Pin for VREF.

### **DDR Input Register**



### Figure 10-5 • DDR Input Register (SSTL2 Class I)

The corresponding structural representations, as generated by SmartGen, are shown below:

DDR\_REG\_DDR\_REG\_0\_inst(.D(Y),.CLK(CLK),.CLR(CLR),.QR(QR),.QF(QF));

#### Verilog

```
module DDR_InBuf_SSTL2_I(PAD,CLR,CLK,QR,QF);
```

input PAD, CLR, CLK; output QR, QF; wire Y; INBUF\_SSTL2\_I INBUF\_SSTL2\_I\_0\_inst(.PAD(PAD),.Y(Y));

endmodule

### VHDL

```
library ieee;
use ieee.std_logic_1164.all;
--The correct library will be inserted automatically by SmartGen
library proasic3; use proasic3.all;
--library fusion; use fusion.all;
--library igloo; use igloo.all;
entity DDR_InBuf_SSTL2_I is
  port(PAD, CLR, CLK : in std_logic; QR, QF : out std_logic) ;
end DDR_InBuf_SSTL2_I;
architecture DEF_ARCH of DDR_InBuf_SSTL2_I is
  component INBUF_SSTL2_I
    port(PAD : in std_logic := 'U'; Y : out std_logic) ;
  end component;
  component DDR_REG
   port(D, CLK, CLR : in std_logic := 'U'; QR, QF : out std_logic) ;
  end component;
signal Y : std_logic ;
begin
  INBUF_SSTL2_I_0_inst : INBUF_SSTL2_I
  port map(PAD => PAD, Y => Y);
  DDR_REG_0_inst : DDR_REG
  port map(D => Y, CLK => CLK, CLR => CLR, QR => QR, QF => QF);
end DEF_ARCH;
```

Table 12-5 • FlashLock Security Options for Fusion						
Security Option	FlashROM Only	FPGA Core Only	FB Co			

Security Option	FlashROM Only	FPGA Core Only	FB Core Only	All
No AES / no FlashLock	-	-	-	_
FlashLock	<i>✓</i>	✓	~	✓
AES and FlashLock	<i>✓</i>	✓	1	1

For this scenario, generate the programming file as follows:

1. Select only the **Security settings** option, as indicated in Figure 12-14 and Figure 12-15 on page 318. Click **Next**.

Figure 12-14 • Programming IGLOO and ProASIC3 Security Settings Only

## **FlashROM and Programming Files**

Each low power flash device has 1 kbit of on-chip, nonvolatile flash memory that can be accessed from the FPGA core. This nonvolatile FlashROM is arranged in eight pages of 128 bits (Figure 13-3). Each page can be programmed independently, with or without the 128-bit AES encryption. The FlashROM can only be programmed via the IEEE 1532 JTAG port and cannot be programmed from the FPGA core. In addition, during programming of the FlashROM, the FPGA core is powered down automatically by the on-chip programming control logic.

						Ву	∕te Nı	umbe	er in F	Page							
		15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
	7																
	6																
be	5																
L m	4																
Z Ø	3																
ag	2																
₽.	1																
	0																

#### Figure 13-3 • FlashROM Architecture

When using FlashROM combined with AES, many subscription-based applications or device serialization applications are possible. The FROM configurator found in the Libero SoC Catalog supports easy management of the FlashROM contents, even over large numbers of devices. The FROM configurator can support FlashROM contents that contain the following:

- Static values
- Random numbers
- Values read from a file
- Independent updates of each page

In addition, auto-incrementing of fields is possible. In applications where the FlashROM content is different for each device, you have the option to generate a single STAPL file for all the devices or individual serialization files for each device. For more information on how to generate the FlashROM content for device serialization, refer to the "FlashROM in Microsemi's Low Power Flash Devices" section on page 133.

Libero SoC includes a unique tool to support the generation and management of FlashROM and FPGA programming files. This tool is called FlashPoint.

Depending on the applications, designers can use the FlashPoint software to generate a STAPL file with different contents. In each case, optional AES encryption and/or different security settings can be set.

In Designer, when you click the Programming File icon, FlashPoint launches, and you can generate STAPL file(s) with four different cases (Figure 13-4 on page 334). When the serialization feature is used during the configuration of FlashROM, you can generate a single STAPL file that will program all the devices or an individual STAPL file for each device.

The following cases present the FPGA core and FlashROM programming file combinations that can be used for different applications. In each case, you can set the optional security settings (FlashLock Pass Key and/or AES Key) depending on the application.

- 1. A single STAPL file or multiple STAPL files with multiple FlashROM contents and the FPGA core content. A single STAPL file will be generated if the device serialization feature is not used. You can program the whole FlashROM or selectively program individual pages.
- 2. A single STAPL file for the FPGA core content

## **Circuit Description**

All IGLOO devices as well as the ProASIC3L product family are available in two versions: V5 devices, which are powered by a 1.5 V supply and V2 devices, which are powered by a supply anywhere in the range of 1.2 V to 1.5 V in 50 mV increments. Applications that use IGLOO or ProASIC3L devices powered by a 1.2 V core supply must have a mechanism that switches the core voltage from 1.2 V (or other voltage below 1.5 V) to 1.5 V during in-system programming (ISP). There are several possible techniques to meet this requirement. Microsemi recommends utilizing a linear voltage regulator, a resistor voltage divider, and an N-Channel Digital FET to set the appropriate VCC voltage, as shown in Figure 14-1.

Where 1.2 V is mentioned in the following text, the meaning applies to any voltage below the 1.5 V range. Resistor values in the figures have been calculated for 1.2 V, so refer to power regulator datasheets if a different core voltage is required.

The main component of Microsemi's recommended circuit is the LTC3025 linear voltage regulator from LinearTech. The output voltage of the LTC3025 on the OUT pin is set by the ratio of two external resistors, R37 and R38, in a voltage divider. The linear voltage regulator adjusts the voltage on the OUT pin to maintain the ADJ pin voltage at 0.4 V (referenced to ground). By using an R38 value of 40.2 k $\Omega$  and an R37 value of 80.6 k $\Omega$ , the output voltage on the OUT pin is 1.2 V. To achieve 1.5 V on the OUT pin, R44 can be used in parallel with R38. The OUT pin can now be used as a switchable source for the VCC supply. Refer to the *LTC3025 Linear Voltage Regulator datasheet* for more information.

In Figure 14-1, the N-Channel Digital FET is used to enable and disable R44. This FET is controlled by the JTAG TRST signal driven by the FlashPro3 programmer. During programming of the device, the TRST signal is driven HIGH by the FlashPro3, and turns the N-Channel Digital FET ON. When the FET is ON, R44 becomes enabled as a parallel resistance to R38, which forces the regulator to set OUT to 1.5 V.

When the FlashPro3 is connected and not in programming mode or when it is not connected, the pulldown resistor, R10, will pull the TRST signal LOW. When this signal is LOW, the N-Channel Digital FET is "open" and R44 is not part of the resistance seen by the LTC3025. The new resistance momentarily changes the voltage value on the ADJ pin, which in turn causes the output of the LTC3025 to compensate by setting OUT to 1.2 V. Now the device will run in regular active mode at the regular 1.2 V core voltage.

Figure 14-1 • Circuit Diagram

## **UJTAG Macro**

The UJTAG tiles can be instantiated in a design using the UJTAG macro from the Fusion, IGLOO, or ProASIC3 macro library. Note that "UJTAG" is a reserved name and cannot be used for any other userdefined blocks. A block symbol of the UJTAG tile macro is presented in Figure 17-2. In this figure, the ports on the left side of the block are connected to the JTAG TAP Controller, and the right-side ports are accessible by the FPGA core VersaTiles. The TDI, TMS, TDO, TCK, and TRST ports of UJTAG are only provided for design simulation purposes and should be treated as external signals in the design netlist. However, these ports must NOT be connected to any I/O buffer in the netlist. Figure 17-3 on page 366 illustrates the correct connection of the UJTAG macro to the user design netlist. Microsemi Designer software will automatically connect these ports to the TAP during place-and-route. Table 17-2 gives the port descriptions for the rest of the UJTAG ports:

Port	Description
UIREG [7:0]	This 8-bit bus carries the contents of the JTAG Instruction Register of each device. Instruction Register values 16 to 127 are not reserved and can be employed as user-defined instructions.
URSTB	URSTB is an active-low signal and will be asserted when the TAP Controller is in Test-Logic-Reset mode. URSTB is asserted at power-up, and a power-on reset signal resets the TAP Controller. URSTB will stay asserted until an external TAP access changes the TAP Controller state.
UTDI	This port is directly connected to the TAP's TDI signal.
UTDO	This port is the user TDO output. Inputs to the UTDO port are sent to the TAP TDO output MUX when the IR address is in user range.
UDRSH	Active-high signal enabled in the ShiftDR TAP state
UDRCAP	Active-high signal enabled in the CaptureDR TAP state
UDRCK	This port is directly connected to the TAP's TCK signal.
UDRUPD	Active-high signal enabled in the UpdateDR TAP state

Table 17-2 • UJTAG Port Descriptions



Figure 17-2 • UJTAG Tile Block Symbol

## Fine Tuning

In some applications, design constants or parameters need to be modified after programming the original design. The tuning process can be done using the UJTAG tile without reprogramming the device with new values. If the parameters or constants of a design are stored in distributed registers or embedded SRAM blocks, the new values can be shifted onto the JTAG TAP Controller pins, replacing the old values. The UJTAG tile is used as the "bridge" for data transfer between the JTAG pins and the FPGA VersaTiles or SRAM logic. Figure 17-5 shows a flow chart example for fine-tuning application steps using the UJTAG tile.

In Figure 17-5, the TMS signal sets the TAP Controller state machine to the appropriate states. The flow mainly consists of two steps: a) shifting the defined instruction and b) shifting the new data. If the target parameter is constantly used in the design, the new data can be shifted into a temporary shift register from UTDI. The UDRSH output of UJTAG can be used as a shift-enable signal, and UDRCK is the shift clock to the shift register. Once the shift process is completed and the TAP Controller state is moved to the Update\_DR state, the UDRUPD output of the UJTAG can latch the new parameter value from the temporary register into a permanent location. This avoids any interruption or malfunctioning during the serial shift of the new value.



Figure 17-5 • Flow Chart Example of Fine-Tuning an Application Using UJTAG